Weimin M Chen

List of Publications by Year in Descending Order

435 papers	7,699 citations	39 h-index	71 g-index
468 ext. papers	8,466 ext. citations	4.1 avg, IF	5.48 L-index

#	Paper	IF	Citations
435	Spontaneous exciton dissociation enables spin state interconversion in delayed fluorescence organic semiconductors. *Nature Communications*, **2021**, 12, 6640	17.4	5
434	An Efficient Deep-Subwavelength Second Harmonic Nanoantenna Based on Surface Plasmon-Coupled Dilute Nitride GaNP Nanowires. *Nano Letters*, **2021**, 21, 3426-3434	11.5	2
433	A high-conductivity n-type polymeric ink for printed electronics. *Nature Communications*, **2021**, 12, 2354	17.4	49
432	Anomalously Strong Second-Harmonic Generation in GaAs Nanowires via Crystal-Structure Engineering. *Advanced Functional Materials*, **2021**, 31, 2104671	15.6	1
431	Competition between triplet pair formation and excimer-like recombination controls singlet fission yield. *Cell Reports Physical Science*, **2021**, 2, 100339	6.1	5
430	Magneto-optical properties of Cr3+ in □Ga2O3. *Applied Physics Letters*, **2021**, 119, 052101	3.4	8
429	Identifying a Generic and Detrimental Role of Fano Resonance in Spin Generation in Semiconductor Nanostructures. *Physical Review Letters*, **2021**, 127, 127401	7.4	0
428	Magnetizing lead-free halide double perovskites. *Science Advances*, **2020**, 6,	14.3	25
427	Effect of Crystal Symmetry on the Spin States of Fe and Vibration Modes in Lead-free Double-Perovskite CsAgBi(Fe)Br. *Journal of Physical Chemistry Letters*, **2020**, 11, 4873-4878	6.4	3
426	Effects of thermal annealing on localization and strain in core/multishell GaAs/GaNAs/GaAs nanowires. *Scientific Reports*, **2020**, 10, 8216	4.9	2
425	Outermost AlGaO x native oxide as a protection layer for GaAs/AlGaAs core-multishell nanowires. *Applied Physics Express*, **2020**, 13, 075003	2.4	2
424	Thermal-annealing effects on energy level alignment at organic heterojunctions and corresponding voltage losses in all-polymer solar cells. *Nano Energy*, **2020**, 72, 104677	17.1	7
423	Ground-state electron transfer in all-polymer donor-acceptor heterojunctions. *Nature Materials*, **2020**, 19, 738-744	27	56
422	Scattering symmetry-breaking induced spin photocurrent from out-of-plane spin texture in a 3D topological insulator. *Scientific Reports*, **2020**, 10, 10610	4.9	2
421	Effects of Bi incorporation on recombination processes in wurtzite GaBiAs nanowires. *Nanotechnology*, **2020**, 31, 225706	3.4	1
420	Formation, electronic structure, and optical properties of self-assembled quantum-dot single-photon emitters in Ga(N,As,P) nanowires. *Physical Review Materials*, **2020**, 4,	3.2	3
419	Gallium vacancies□common non-radiative defects in ternary GaAsP and quaternary GaNAsP nanowires. *Nano Express*, **2020**, 1, 020022	2	0

418	Vibronic coherence contributes to photocurrent generation in organic semiconductor heterojunction diodes. *Nature Communications*, **2020**, 11, 617	17.4	14
417	Effects of growth temperature and thermal annealing on optical quality of GaNAs nanowires emitting in the near-infrared spectral range. *Nanotechnology*, **2020**, 31, 065702	3.4	3
416	Self-assembled nanodisks in coaxial GaAs/GaAsBi/GaAs core-multishell nanowires. *Nanoscale*, **2020**, 12, 20849-20858	7.7	1
415	Sequential Doping of Ladder-Type Conjugated Polymers for Thermally Stable n-Type Organic Conductors. *ACS Applied Materials & Interfaces*, **2020**, 12, 53003-53011	9.5	21
414	Near-Infrared Light-Responsive Cu-Doped Cs2AgBiBr6. *Advanced Functional Materials*, **2020**, 30, 2005521	15.6	17
413	Fine Structure and Spin Dynamics of Linearly Polarized Indirect Excitons in Two-Dimensional CdSe/CdTe Colloidal Heterostructures. *ACS Nano*, **2019**, 13, 10140-10153	16.7	8
412	Impact of Singly Occupied Molecular Orbital Energy on the n-Doping Efficiency of Benzimidazole Derivatives. *ACS Applied Materials & Interfaces*, **2019**, 11, 37981-37990	9.5	17
411	Identification of a Nitrogen-related acceptor in ZnO nanowires. *Nanoscale*, **2019**, 11, 10921-10926	7.7	4
410	Measurements of Strain and Bandgap of Coherently Epitaxially Grown Wurtzite InAsP-InP Core-Shell Nanowires. *Nano Letters*, **2019**, 19, 2674-2681	11.5	11
409	Dilute nitrides-based nanowires-a promising platform for nanoscale photonics and energy technology. *Nanotechnology*, **2019**, 30, 292002	3.4	6
408	Effect of Backbone Regiochemistry on Conductivity, Charge Density, and Polaron Structure of n-Doped Donor-Acceptor Polymers. *Chemistry of Materials*, **2019**, 31, 3395-3406	9.6	31
407	Molecular beam epitaxial growth of dilute nitride GaNAs and GaInNAs nanowires. *Nanotechnology*, **2019**, 30, 244002	3.4	5
406	Effect of exciton transfer on recombination dynamics in vertically nonuniform GaAsSb epilayers. *Applied Physics Letters*, **2019**, 114, 252101	3.4	7
405	Effects of N implantation on defect formation in ZnO nanowires. *Thin Solid Films*, **2019**, 687, 137449	2.2	8
404	Increasing N content in GaNAsP nanowires suppresses the impact of polytypism on luminescence. *Nanotechnology*, **2019**, 30, 405703	3.4	3
403	Band Structure of Wurtzite GaBiAs Nanowires. *Nano Letters*, **2019**, 19, 6454-6460	11.5	5
402	Nonequilibrium site distribution governs charge-transfer electroluminescence at disordered organic heterointerfaces. *Proceedings of the National Academy of Sciences of the United States of America*, **2019**, 116, 23416-23425	11.5	20
401	Electron paramagnetic resonance signatures of Co2+ and Cu2+ in □Ga2O3. *Applied Physics Letters*, **2019**, 115, 242101	3.4	6

400	Near-Infrared Lasing at 1 □m from a Dilute-Nitride-Based Multishell Nanowire. *Nano Letters*, **2019**, 19, 885-890	11.5	18
399	A Free-Standing High-Output Power Density Thermoelectric Device Based on Structure-Ordered PEDOT:PSS. *Advanced Electronic Materials*, **2018**, 4, 1700496	6.4	58
398	Effect of a Phonon Bottleneck on Exciton and Spin Generation in Self-Assembled In1□GaxAs Quantum Dots. *Physical Review Applied*, **2018**, 9,	4.3	3
397	Effects of Strong Band-Tail States on Exciton Recombination Dynamics in Dilute Nitride GaP/GaNP Core/Shell Nanowires. *Journal of Physical Chemistry C*, **2018**, 122, 19212-19218	3.8	7
396	Design rules for minimizing voltage losses in high-efficiency organic solar cells. *Nature Materials*, **2018**, 17, 703-709	27	500
395	GaAs/GaNAs core-multishell nanowires with nitrogen composition exceeding 2%. *Applied Physics Letters*, **2018**, 113, 011901	3.4	10
394	Efficient Auger Charge-Transfer Processes in ZnO. *Physical Review Applied*, **2018**, 9,	4.3	1
393	N-induced Quantum Dots in GaAs/Ga(N,As) Core/Shell Nanowires: Symmetry, Strain, and Electronic Structure. *Physical Review Applied*, **2018**, 10,	4.3	5
392	Room-temperature polarized spin-photon interface based on a semiconductor nanodisk-in-nanopillar structure driven by few defects. *Nature Communications*, **2018**, 9, 3575	17.4	12
391	Effect of Side Groups on the Photovoltaic Performance Based on Porphyrin-Perylene Bisimide Electron Acceptors. *ACS Applied Materials & Interfaces*, **2018**, 10, 32454-32461	9.5	15
390	Charge Generation via Relaxed Charge-Transfer States in Organic Photovoltaics by an Energy-Disorder-Driven Entropy Gain. *Journal of Physical Chemistry C*, **2018**, 122, 12640-12646	3.8	19
389	Photon upconversion promoted by defects in low-dimensional semiconductor nanostructures **2018**, 189-210		1
388	Defects in one-dimensional nanowires **2018**, 63-85		1
387	Defect-enabled room-temperature spin functionalities in a nonmagnetic semiconductor **2018**, 265-284		
386	Effects of Nitrogen Incorporation on Structural and Optical Properties of GaNAsP Nanowires. *Journal of Physical Chemistry C*, **2017**, 121, 7047-7055	3.8	9
385	Luminescent and Optically Detected Magnetic Resonance Studies of CdS/PVA Nanocomposite. *Nanoscale Research Letters*, **2017**, 12, 130	5	8
384	Dilute Nitride Nanowire Lasers Based on a GaAs/GaNAs Core/Shell Structure. *Nano Letters*, **2017**, 17, 1775-1781	11.5	36
383	Spin injection and helicity control of surface spin photocurrent in a three dimensional topological insulator. *Nature Communications*, **2017**, 8, 15401	17.4	27

382	Room Temperature Defect-Engineered Spin Functionalities: Concept and Optimization **2017**, 33-54		
381	GaNAs-Based Nanowires for Near-Infrared Optoelectronics **2017**, 133-159		
380	Novel GaNP Nanowires for Advanced Optoelectronics and Photonics **2017**, 107-132		
379	Spectroelectrochemistry and Nature of Charge Carriers in Self-Doped Conducting Polymer. *Advanced Electronic Materials*, **2017**, 3, 1700096	6.4	25
378	Strongly polarized quantum-dot-like light emitters embedded in GaAs/GaNAs core/shell nanowires. *Nanoscale*, **2016**, 8, 15939-47	7.7	19
377	Unintentional nitrogen incorporation in ZnO nanowires detected by electron paramagnetic resonance spectroscopy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2016**, 13, 572-575		1
376	Understanding and optimizing spin injection in self-assembled InAs/GaAs quantum-dot molecular structures. *Nano Research*, **2016**, 9, 602-611	10	6
375	Structural properties of GaNAs nanowires probed by micro-Raman spectroscopy. *Semiconductor Science and Technology*, **2016**, 31, 025002	1.8	1
374	Core□shell carrier and exciton transfer in GaAs/GaNAs coaxial nanowires. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2016**, 34, 04J104	1.3	5
373	Thermal stability of the prominent compensating (AlZn□VZn) center in ZnO. *Journal of Applied Physics*, **2016**, 119, 105702	2.5	6
372	Defect formation in GaAs/GaNxAs1-x core/shell nanowires. *Applied Physics Letters*, **2016**, 109, 203103	3.4	10
371	Phosphorescence of CdS nanoparticles in polymer matrix as an indication of host-guest interaction. *Materials Chemistry and Physics*, **2016**, 177, 379-383	4.4	2
370	Growth of isotopically enriched ZnO nanorods of excellent optical quality. *Journal of Crystal Growth* , **2015**, 429, 6-12	1.6	10
369	Effects of Polytypism on Optical Properties and Band Structure of Individual Ga(N)P Nanowires from Correlative Spatially Resolved Structural and Optical Studies. *Nano Letters*, **2015**, 15, 4052-8	11.5	16
368	Interfacial bonding in a CdS/PVA nanocomposite: A Raman scattering study. *Journal of Colloid and Interface Science*, **2015**, 452, 33-37	9.3	14
367	Enhancement of polymer endurance to UV light by incorporation of semiconductor nanoparticles. *Nanoscale Research Letters*, **2015**, 10, 81	5	21
366	Exciton Fine-Structure Splitting in Self-Assembled Lateral InAs/GaAs Quantum-Dot Molecular Structures. *ACS Nano*, **2015**, 9, 5741-9	16.7	4
365	Dual-wavelength excited photoluminescence spectroscopy of deep-level hole traps in Ga(In)NP. *Journal of Applied Physics*, **2015**, 117, 015701	2.5	2

364	Size dependence of electron spin dephasing in InGaAs quantum dots. *Applied Physics Letters*, **2015**, 106, 093109	3.4	4
363	Optimizing GaNP coaxial nanowires for efficient light emission by controlling formation of surface and interfacial defects. *Nano Letters*, **2015**, 15, 242-7	11.5	15
362	Suppression of non-radiative surface recombination by N incorporation in GaAs/GaNAs core/shell nanowires. *Scientific Reports*, **2015**, 5, 11653	4.9	27
361	Efficient nitrogen incorporation in ZnO nanowires. *Scientific Reports*, **2015**, 5, 13406	4.9	17
360	Fabry-Perot Microcavity Modes in Single GaP/GaNP Core/Shell Nanowires. *Small*, **2015**, 11, 6331-7	11	10
359	Turning ZnO into an Efficient Energy Upconversion Material by Defect Engineering. *Advanced Functional Materials*, **2014**, 24, 3760-3764	15.6	32
358	Identification of an isolated arsenic antisite defect in GaAsBi. *Applied Physics Letters*, **2014**, 104, 052110	3.4	16
357	Semi-metallic polymers. *Nature Materials*, **2014**, 13, 190-4	27	605
356	Origin of strong photoluminescence polarization in GaNP nanowires. *Nano Letters*, **2014**, 14, 5264-9	11.5	17
355	Trap-Assisted Recombination via Integer Charge Transfer States in Organic Bulk Heterojunction Photovoltaics. *Advanced Functional Materials*, **2014**, 24, 6309-6316	15.6	60
354	Growth and characterization of dilute nitride GaNxP1□ nanowires and GaNxP1□/GaNyP1□ core/shell nanowires on Si (111) by gas source molecular beam epitaxy. *Applied Physics Letters*, **2014**, 105, 072107	3.4	29
353	Zinc-Vacancy□Donor Complex: A Crucial Compensating Acceptor in ZnO. *Physical Review Applied*, **2014**, 2,	4.3	45
352	Energy upconversion in GaP/GaNP core/shell nanowires for enhanced near-infrared light harvesting. *Small*, **2014**, 10, 4403-8	11	22
351	Magneto-optical properties and recombination dynamics of isoelectronic bound excitons in ZnO **2014**,		1
350	Defect properties of ZnO nanowires **2014**,		4
349	Origin of radiative recombination and manifestations of localization effects in GaAs/GaNAs core/shell nanowires. *Applied Physics Letters*, **2014**, 105, 253106	3.4	24
348	Raman spectroscopy of GaP/GaNP core/shell nanowires. *Applied Physics Letters*, **2014**, 105, 193102	3.4	18
347	Limiting factor of defect-engineered spin-filtering effect at room temperature. *Physical Review B*, **2014**, 89,	3.3	3

346	Anomalous spectral dependence of optical polarization and its impact on spin detection in InGaAs/GaAs quantum dots. *Applied Physics Letters*, **2014**, 105, 132106	3.4	10
345	Kidneys from standard-criteria donors with different severities of terminal acute kidney injury. *Transplantation Proceedings*, **2014**, 46, 3335-8	1.1	9
344	Spin dynamics of isoelectronic bound excitons in ZnO. *Physical Review B*, **2014**, 89,	3.3	1
343	Effects of Ni-coating on ZnO nanowires: A Raman scattering study. *Journal of Applied Physics*, **2013**, 113, 214302	2.5	15
342	Effect of the detonation nanodiamond surface on the catalytic activity of deposited nickel catalysts in the hydrogenation of acetylene. *Russian Journal of Physical Chemistry A*, **2013**, 87, 1114-1120	0.7	8
341	Cathodoluminescence characterization of ZnO tetrapod structures. *Thin Solid Films*, **2013**, 543, 114-117	2.2	6
340	Effect of thermal annealing on defects in post-growth hydrogenated GaNP. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 561-563		1
339	Optical properties of GaP/GaNP core/shell nanowires: a temperature-dependent study. *Nanoscale Research Letters*, **2013**, 8, 239	5	6
338	Room-temperature electron spin amplifier based on Ga(In)NAs alloys. *Advanced Materials*, **2013**, 25, 738-42	24	21
337	Defect properties of ZnO nanowires revealed from an optically detected magnetic resonance study. *Nanotechnology*, **2013**, 24, 015701	3.4	15
336	Efficient room-temperature nuclear spin hyperpolarization of a defect atom in a semiconductor. *Nature Communications*, **2013**, 4, 1751	17.4	29
335	Dynamics of donor bound excitons in ZnO. *Applied Physics Letters*, **2013**, 102, 121103	3.4	14
334	Role of the host polymer matrix in light emission processes in nano-CdS/poly vinyl alcohol composite. *Thin Solid Films*, **2013**, 543, 11-15	2.2	9
333	Defects in N, O and N, Zn implanted ZnO bulk crystals. *Journal of Applied Physics*, **2013**, 113, 103509	2.5	31
332	Optically detected magnetic resonance studies of point defects in quaternary GaNAsP epilayers grown by vapor phase epitaxy. *Applied Physics Letters*, **2013**, 102, 021910	3.4	9
331	Effect of hyperfine-induced spin mixing on the defect-enabled spin blockade and spin filtering in GaNAs. *Physical Review B*, **2013**, 87,	3.3	10
330	Efficient upconversion of photoluminescence via two-photon absorption in bulk and nanorod ZnO. *Applied Physics B: Lasers and Optics*, **2012**, 108, 919-924	1.9	21
329	Effects of Ultraviolet Light on Optical Properties of Colloidal CdS Nanoparticles Embedded in Polyvinyl Alcohol (PVA) Matrix. *Advanced Science, Engineering and Medicine*, **2012**, 4, 394-400	0.6	11

328	Effects of hydrogenation on non-radiative defects in GaNP and GaNAs alloys: An optically detected magnetic resonance study. *Journal of Applied Physics*, **2012**, 111, 023501	2.5	4
327	Mechanism for radiative recombination and defect properties of GaP/GaNP core/shell nanowires. *Applied Physics Letters*, **2012**, 101, 163106	3.4	27
326	Antiferromagnetic interaction in coupled CdSe/ZnMnSe quantum dot structures. *Applied Physics Letters*, **2012**, 101, 052405	3.4	4
325	Optically Detected Magnetic Resonance of Defects in Semiconductors. *Progress in Theoretical Chemistry and Physics*, **2012**, 345-366	0.6	
324	The Hanle effect and electron spin polarization in InAs/GaAs quantum dots up to room temperature. *Nanotechnology*, **2012**, 23, 135705	3.4	4
323	Effects of P implantation and post-implantation annealing on defect formation in ZnO. *Journal of Applied Physics*, **2012**, 111, 043520	2.5	6
322	Long delays of light in ZnO caused by exciton-polariton propagation. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 1307-1311	1.3	
321	Catalytic conversion of C2-C3 alcohols on detonation nanodiamond and its modifications. *Russian Journal of Physical Chemistry A*, **2012**, 86, 26-31	0.7	17
320	Efficient room-temperature spin detector based on GaNAs. *Journal of Applied Physics*, **2012**, 111, 07C303	2.5	9
319	Effects of a longitudinal magnetic field on spin injection and detection in InAs/GaAs quantum dot structures. *Journal of Physics Condensed Matter*, **2012**, 24, 145304	1.8	3
318	Evidence for coupling between exciton emissions and surface plasmon in Ni-coated ZnO nanowires. *Nanotechnology*, **2012**, 23, 425201	3.4	30
317	Sub-millisecond dynamic nuclear spin hyperpolarization in a semiconductor: A case study from PIn antisite in InP. *Physical Review B*, **2012**, 86,	3.3	2
316	Zeeman splitting and dynamics of an isoelectronic bound exciton near the band edge of ZnO. *Physical Review B*, **2012**, 86,	3.3	5
315	Temperature dependence of dynamic nuclear polarization and its effect on electron spin relaxation and dephasing in InAs/GaAs quantum dots. *Applied Physics Letters*, **2012**, 100, 143105	3.4	4
314	Donor bound excitons involving a hole from the B valence band in ZnO: Time resolved and magneto-photoluminescence studies. *Applied Physics Letters*, **2011**, 99, 091909	3.4	7
313	Room-temperature spin injection and spin loss across a GaNAs/GaAs interface. *Applied Physics Letters*, **2011**, 98, 012112	3.4	7
312	Polyol-thermal synthesis of silver nanowires for Hg2+ sensing detection. *Journal of Nanoparticle Research*, **2011**, 13, 5087-5101	2.3	11
311	Slowdown of light due to exciton-polariton propagation in ZnO. *Physical Review B*, **2011**, 83,	3.3	12

310	Room temperature spin filtering effect in GaNAs: Role of hydrogen. *Applied Physics Letters*, **2011**, 99, 152109	3.4	7
309	Effect of postgrowth hydrogen treatment on defects in GaNP. *Applied Physics Letters*, **2011**, 98, 141920	3.4	7
308	Strong room-temperature optical and spin polarization in InAs/GaAs quantum dot structures. *Applied Physics Letters*, **2011**, 98, 203110	3.4	14
307	On the origin of suppression of free exciton no-phonon emission in ZnO tetrapods. *Applied Physics Letters*, **2010**, 96, 033108	3.4	11
306	Evidence for a phosphorus-related interfacial defect complex at a GaP/GaNP heterojunction. *Physical Review B*, **2010**, 81,	3.3	10
305	Long lifetime of free excitons in ZnO tetrapod structures. *Applied Physics Letters*, **2010**, 96, 083104	3.4	26
304	Electron spin filtering by thin GaNAs/GaAs multiquantum wells. *Applied Physics Letters*, **2010**, 96, 052104	3.4	25
303	Efficiency of spin injection in novel InAs quantum dot structures: exciton vs. free carrier injection. *Journal of Physics: Conference Series*, **2010**, 245, 012044	0.3	4
302	Spin Dynamics in ZnO-Based Materials. *Journal of Superconductivity and Novel Magnetism*, **2010**, 23, 161-165	1.5	7
301	Paramagnetic centers in detonation nanodiamonds studied by CW and pulse EPR. *Chemical Physics Letters*, **2010**, 493, 319-322	2.5	19
300	Dominant recombination centers in Ga(In)NAs alloys: Ga interstitials. *Applied Physics Letters*, **2009**, 95, 241904	3.4	54
299	Spin injection in lateral InAs quantum dot structures by optical orientation spectroscopy. *Nanotechnology*, **2009**, 20, 375401	3.4	12
298	Electron spin control in dilute nitride semiconductors. *Journal of Physics Condensed Matter*, **2009**, 21, 174211	1.8	13
297	Propagation dynamics of exciton spins in a high-density semiconductor quantum dot system. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 50-52		
296	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. *Nature Materials*, **2009**, 8, 198-202	27	78
295	Effects of Ga doping on optical and structural properties of ZnO epilayers. *Superlattices and Microstructures*, **2009**, 45, 413-420	2.8	8
294	Transfer dynamics of spin-polarized excitons into semiconductor quantum dots. *Journal of Luminescence*, **2009**, 129, 1927-1930	3.8	1
293	Oxygen and zinc vacancies in as-grown ZnO single crystals. *Journal Physics D: Applied Physics*, **2009**, 42, 175411	3	106

292	Effects of hydrogen on the optical properties of ZnCdO/ZnO quantum wells grown by molecular beam epitaxy. *Applied Physics Letters*, **2008**, 92, 261912	3.4	21
291	Formation of grown-in defects in molecular beam epitaxial Ga(In)NP: Effects of growth conditions and postgrowth treatments. *Journal of Applied Physics*, **2008**, 103, 063519	2.5	14
290	Migration and luminescence enhancement effects of deuterium in ZnO/ZnCdO quantum wells. *Applied Physics Letters*, **2008**, 92, 032103	3.4	10
289	Dominant factors limiting efficiency of optical spin detection in ZnO-based materials. *Applied Physics Letters*, **2008**, 92, 092103	3.4	17
288	Spin-Conserving Tunneling of Excitons in Diluted Magnetic Semiconductor Double Quantum Wells. *Japanese Journal of Applied Physics*, **2008**, 47, 3533-3536	1.4	4
287	Effects of stoichiometry on defect formation in ZnO epilayers grown by molecular-beam epitaxy: An optically detected magnetic resonance study. *Journal of Applied Physics*, **2008**, 103, 023712	2.5	17
286	Impact of the strained SiGe source/drain on hot carrier reliability for 45nm p-type metal-oxide-semiconductor field-effect transistors. *Applied Physics Letters*, **2008**, 92, 133504	3.4	8
285	Efficiency of optical spin injection and spin loss from a diluted magnetic semiconductor ZnMnSe to CdSe nonmagnetic quantum dots. *Physical Review B*, **2008**, 77,	3.3	14
284	Magneto-optical and tunable laser excitation spectroscopy of spin-injection and spin loss from Zn(Cd)MnSe diluted magnetic quantum well to CdSe non-magnetic quantum dots. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2008**, 147, 262-266	3.1	1
283	Spin injection in a coupled system of a diluted magnetic semiconductor Zn0.80Mn0.20Se and self-assembled quantum dots of CdSe. *Superlattices and Microstructures*, **2008**, 43, 615-619	2.8	
282	Effect of growth conditions on grown-in defect formation and luminescence efficiency in Ga(In)NP epilayers grown by molecular-beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 460-463		
281	Effects of grown-in defects on electron spin polarization in dilute nitride alloys. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1529-1531		
280	Optical and electronic properties of GaInNP alloys □a new material system for lattice matching to GaAs. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 101-106	1.6	1
279	Spin resonance spectroscopy of grown-in defects in Ga(In)NP alloys. *Superlattices and Microstructures*, **2008**, 43, 620-625	2.8	
278	Optical and Electronic Properties of GaInNP Alloys: A New Material for Lattice Matching to GaAs **2008**, 301-316		
277	Optically detected cyclotron resonance studies of InxGa1□xNyAs1□y□GaAs quantum wells sandwiched between type-II AlAs□GaAs superlattices. *Journal of Applied Physics*, **2007**, 101, 073705	2.5	3
276	Optical characterization studies of grown-in defects in ZnO epilayers grown by molecular beam epitaxy. *Physica B: Condensed Matter*, **2007**, 401-402, 413-416	2.8	4
275	. *IEEE Transactions on Electron Devices*, **2007**, 54, 1040-1048	2.9	121

274	Mechanism for radiative recombination in ZnCdO alloys. *Applied Physics Letters*, **2007**, 90, 261907	3.4	23
273	Ferromagnetism in Transition-Metal Doped ZnO. *Journal of Electronic Materials*, **2007**, 36, 462-471	1.9	80
272	Metamorphic InGaAs quantum wells for light emission at 1.31–1.6 μm. *Thin Solid Films*, **2007**, 515, 4348-4351	1.2	6
271	Dynamics of exciton-spin injection, transfer, and relaxation in self-assembled quantum dots of CdSe coupled with a diluted magnetic semiconductor layer of Zn0.80Mn0.20Se. *Physical Review B*, **2007**, 75,	3.3	22
270	Transition Metal Doped ZnO for Spintronics. *Materials Research Society Symposia Proceedings*, **2007**, 999, 1		3
269	Prospects of Potential Semiconductor Spin Detectors. *Solid State Phenomena*, **2007**, 124-126, 839-842	0.4	
268	Magneto-optical spectroscopy of spin injection and spin relaxation in ZnMnSe/ZnCdSe and GaMnN/InGaN spin light-emitting structures. *Physica Status Solidi (A) Applications and Materials Science*, **2007**, 204, 159-173	1.6	1
267	Hydrogen passivation of nitrogen in GaNAs and GaNP alloys: How many H atoms are required for each N atom?. *Applied Physics Letters*, **2007**, 90, 021920	3.4	6
266	Point defects in dilute nitride III-N-As and III-N-P. *Physica B: Condensed Matter*, **2006**, 376-377, 545-551	2.8	20
265	On a possible origin of the 2.87 eV optical transition in GaNP. *Journal of Physics Condensed Matter*, **2006**, 18, 449-457	1.8	1
264	Optical characterization of ZnMnO-based dilute magnetic semiconductor structures. *Journal of Vacuum Science & Technology B*, **2006**, 24, 259		13
263	Investigation of the Electronic Structure of the UD-4 Defect in 4H-SiC by Optical Techniques. *Materials Science Forum*, **2006**, 527-529, 461-464	0.4	0
262	Optical Characterization of Zn1-xCdxO Alloys Grown by Molecular-Beam Epitaxy. *ECS Transactions*, **2006**, 3, 391-398	1	3
261	Intrinsic Paramagnetic Defects in GaNP Alloys Grown on Silicon. *ECS Transactions*, **2006**, 3, 231-236	1	
260	Density-dependent dynamics of exciton magnetic polarons in ZnMnSe-ZnSSe type-II quantum wells. *Physical Review B*, **2006**, 73,	3.3	8
259	Photoluminescence upconversion in GaInNP-GaAs heterostructures grown by gas source molecular beam epitaxy. *Journal of Applied Physics*, **2006**, 99, 073515	2.5	13
258	Optically detected magnetic resonance studies of point defects in Ga(Al)NAs. *Physical Review B*, **2006**, 73,	3.3	9
257	Effect of nitrogen ion bombardment on defect formation and luminescence efficiency of GaNP epilayers grown by molecular-beam epitaxy. *Applied Physics Letters*, **2006**, 88, 101904	3.4	7

256	Radiative recombination of GaInNP alloys lattice matched to GaAs. *Applied Physics Letters*, **2006**, 88, 011910	3.4	8
255	Modeling of band gap properties of GaInNP alloys lattice matched to GaAs. *Applied Physics Letters*, **2006**, 88, 031907	3.4	12
254	Ferromagnetism in ZnO Doped with Transition Metal Ions **2006**, 555-576		
253	Band gap properties of Zn1−xCdxO alloys grown by molecular-beam epitaxy. *Applied Physics Letters* , **2006**, 89, 151909	3.4	71
252	Unusual effects of hydrogen on electronic and lattice properties of GaNP alloys. *Physica B: Condensed Matter*, **2006**, 376-377, 568-570	2.8	1
251	Signatures of grown-in defects in GaInNP alloys grown on a GaAs substrate from magnetic resonance studies. *Physica B: Condensed Matter*, **2006**, 376-377, 571-574	2.8	
250	Material properties of dilute nitrides: Ga(In)NAs and Ga(In)NP. *Journal of Crystal Growth*, **2006**, 288, 7-11	1.6	2
249	Transient photoluminescence spectroscopy of spin injection dynamics in double quantum wells of diluted magnetic semiconductors. *Journal of Luminescence*, **2006**, 119-120, 418-422	3.8	1
248	Transient Spectroscopy of Optical Spin Injection in ZnMnSe/ZnCdSe Quantum Structures. *Journal of Superconductivity and Novel Magnetism*, **2006**, 18, 371-373		
247	Optical Study of Spin Injection Dynamics in Double Quantum Wells of II-VI Diluted Magnetic Semiconductors. *AIP Conference Proceedings*, **2005**,	0	1
246	Spin injection and spin loss in GaMnN/InGaN Light-Emitting Diodes. *AIP Conference Proceedings*, **2005**,	0	2
245	Formation of Ferromagnetic SiC:Mn Phases. *Materials Science Forum*, **2005**, 483-485, 241-244	0.4	2
244	Investigation of a GaMnN/GaN/InGaN structure for spin LED. *AIP Conference Proceedings*, **2005**,	0	4
243	Effects of rapid thermal annealing on optical properties of GaNxP1−x alloys grown by solid source molecular beam epitaxy. *Semiconductor Science and Technology*, **2005**, 20, 353-356	1.8	7
242	Identification of a dominant mechanism for optical spin injection from a diluted magnetic semiconductor: Spin-conserving energy transfer via localized excitations. *Physical Review B*, **2005**, 72,	3.3	25
241	Efficient spin relaxation in InGaN□GaN and InGaN□GaMnN quantum wells: An obstacle to spin detection. *Applied Physics Letters*, **2005**, 87, 192107	3.4	17
240	Magnetic resonance signatures of grown-in defects in GaInNP alloys grown on a GaAs substrate. *Applied Physics Letters*, **2005**, 86, 222110	3.4	6
239	Band alignment in GaInNP□GaAs heterostructures grown by gas-source molecular-beam epitaxy. *Applied Physics Letters*, **2005**, 86, 261904	3.4	8

238	Properties of Ga-interstitial defects in AlxGa1−xNyP1−y. *Physical Review B*, **2005**, 71,	3.3	36
237	Effect of momentum relaxation on exciton spin dynamics in diluted magnetic semiconductor ZnMnSe□dSe superlattices. *Physical Review B*, **2005**, 71,	3.3	13
236	Defects in Dilute Nitrides. *Acta Physica Polonica A*, **2005**, 108, 571-579	0.6	2
235	Optical study of spin injection dynamics in InGaN□GaN quantum wells with GaMnN injection layers. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 2668		14
234	Identification of Ga-interstitial defects in GaNyP1−y and AlxGa1−xNyP1−y. *Physical Review B*, **2004**, 70,	3.3	18
233	On the origin of spin loss in GaMnN/InGaN light-emitting diodes. *Applied Physics Letters*, **2004**, 84, 2599-2601	3.4	35
232	Experimental evidence for N-induced strong coupling of host conduction band states in GaNxP1−x: Insight into the dominant mechanism for giant band-gap bowing. *Physical Review B*, **2004**, 69,	3.3	25
231	Analysis of band anticrossing in GaNxP1−x alloys. *Physical Review B*, **2004**, 70,	3.3	46
230	Formation of Ga interstitials in (Al,In)yGa1−yNxP1−x alloys and their role in carrier recombination. *Applied Physics Letters*, **2004**, 85, 2827-2829	3.4	14
229	Efficient spin depolarization in ZnCdSe spin detector: an important factor limiting optical spin injection efficiency in ZnMnSe□ZnCdSe spin light-emitting structures. *Applied Physics Letters*, **2004**, 85, 5260-5262	3.4	23
228	Origin of bandgap bowing in GaNP alloys. *IEE Proceedings: Optoelectronics*, **2004**, 151, 389-392		3
227	Effects of rapid thermal annealing on optical quality of GaNP alloys. *IEE Proceedings: Optoelectronics*, **2004**, 151, 335-337		3
226	Defects in dilute nitrides: significance and experimental signatures. *IEE Proceedings: Optoelectronics* , **2004**, 151, 379-384		4
225	Electrical and luminescent properties and the spectra of deep centers in GaMnN/InGaN light-emitting diodes. *Journal of Electronic Materials*, **2004**, 33, 241-247	1.9	2
224	Optical and electrical characterization of (Ga,Mn)N/InGaN multiquantum well light-emitting diodes. *Journal of Electronic Materials*, **2004**, 33, 467-471	1.9	8
223	InAs/Zn(Mn)Te/Cd(Mn)Se pseudomorphic quantum well structures for spintronic applications. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 704-707	1.3	1
222	Exciton magnetic polarons in a type II ZnMnSe/ZnSSe superlattice. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 847-850		3
221	Role of hydrogen in improving optical quality of GaNAs alloys. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 20, 313-316	3	

220	Wide bandgap GaN-based semiconductors for spintronics. *Journal of Physics Condensed Matter*, **2004**, 16, R209-R245	1.8	106
219	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of GaNxP1 alloys: A proof for a general property of dilute nitrides. *Physical Review B*, **2004**, 70,	3.3	21
218	Evaluation of optical quality and defect properties of GaNxP1 alloys lattice matched to Si. *Applied Physics Letters*, **2004**, 85, 6347-6349	3.4	7
217	Defects in dilute nitrides. *Journal of Physics Condensed Matter*, **2004**, 16, S3027-S3035	1.8	26
216	As-Grown 4H-SiC Epilayers with Magnetic Properties. *Materials Science Forum*, **2004**, 457-460, 747-750	0.4	19
215	Influence of conduction-band nonparabolicity on electron confinement and effective mass in GaNxAs1 GaAs quantum wells. *Physical Review B*, **2004**, 69,	3.3	85
214	Electronic Structure of Deep Defects in SiC. *Advanced Texts in Physics*, **2004**, 461-492		7
213	Cyclotron Resonance Studies of Effective Masses and Band Structure in SiC. *Advanced Texts in Physics*, **2004**, 437-460		4
212	Exciton Spin Manipulation in ZnMnSe-Based Structures. *Journal of Superconductivity and Novel Magnetism*, **2003**, 16, 399-402		3
211	PN defect in GaNP studied by optically detected magnetic resonance. *Physica B: Condensed Matter* , **2003**, 340-342, 399-402	2.8	1
210	Identification of Ga interstitials in GaAlNP. *Physica B: Condensed Matter*, **2003**, 340-342, 466-469	2.8	2
209	Hydrogen-related effects in diluted nitrides. *Physica B: Condensed Matter*, **2003**, 340-342, 371-376	2.8	3
208	Recombination processes in N-containing III V ternary alloys. *Solid-State Electronics*, **2003**, 47, 467-475	1.7	39
207	Temperature behavior of the GaNP band gap energy. *Solid-State Electronics*, **2003**, 47, 493-496	1.7	6
206	Magneto-photoluminescence studies of diluted magnetic semiconductor type-II quantum wells ZnMnSe/ZnSSe. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 17, 352-354	3	3
205	Photoluminescence Up-Conversion Processes in SiC. *Materials Science Forum*, **2003**, 433-436, 309-312	0.4	
204	Resonant suppression of exciton spin relaxation in Zn0.96Mn0.04Se/CdSe superlattices. *Journal of Applied Physics*, **2003**, 93, 7352-7354	2.5	3
203	Nitrogen passivation induced by atomic hydrogen: The GaP1 Ny case. *Physical Review B*, **2003**, 67,	3.3	51

202	Hydrogen-induced improvements in optical quality of GaNAs alloys. *Applied Physics Letters*, **2003**, 82, 3662-3664	3.4	45
201	Exciton spin relaxation in diluted magnetic semiconductor Zn1−xMnxSe/CdSe superlattices: Effect of spin splitting and role of longitudinal optical phonons. *Physical Review B*, **2003**, 67,	3.3	31
200	Control of spin functionality in ZnMnSe-based structures: Spin switching versus spin alignment. *Applied Physics Letters*, **2003**, 82, 1700-1702	3.4	20
199	Optically Detected Magnetic Resonance of Defects in Semiconductors. *Progress in Theoretical Chemistry and Physics*, **2003**, 601-625	0.6	5
198	Semimagnetic ZnMnSe/CdSe Fractional Monolayer Superlattice as an Injector of Spin-Polarized Carriers. *Physica Status Solidi (B): Basic Research*, **2002**, 229, 765-768	1.3	4
197	Optical characterization of III-nitrides. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2002**, 93, 112-122	3.1	26
196	On the spin injection in ZnMnSe/ZnCdSe heterostructures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 538-541	3	6
195	Evidence for type I band alignment in GaNAs/GaAs quantum structures by optical spectroscopies. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 1074-1077	3	1
194	ZnMnSe/ZnSSe Type-II semimagnetic superlattices: Growth and magnetoluminescence properties. *Semiconductors*, **2002**, 36, 1288-1293	0.7	5
193	Temperature dependence of the GaNxP1−x band gap and effect of band crossover. *Applied Physics Letters*, **2002**, 81, 3984-3986	3.4	31
192	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and 6H-SiC. *Physical Review B*, **2002**, 66,	3.3	39
191	The Neutral Silicon Vacancy in SiC: Ligand Hyperfine Interaction. *Materials Science Forum*, **2002**, 389-393, 501-504	0.4	8
190	Electronic Structure of the UD3 Defect in 4H- and 6H-SiC. *Materials Science Forum*, **2002**, 389-393, 509-512	0.4	1
189	Time-resolved studies of photoluminescence in GaNxP1−x alloys: Evidence for indirect-direct band gap crossover. *Applied Physics Letters*, **2002**, 81, 52-54	3.4	77
188	Photoluminescence upconversion in 4H-SiC. *Applied Physics Letters*, **2002**, 81, 2547-2549	3.4	3
187	UD-3 defect in 4H, 6H, and 15R SiC: Electronic structure and phonon coupling. *Physical Review B*, **2002**, 66,	3.3	13
186	Magneto-optical and light-emission properties of III-As-N semiconductors. *Semiconductor Science and Technology*, **2002**, 17, 815-822	1.8	39
185	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. *Applied Physics Letters*, **2002**, 81, 2196-2198	3.4	29

184	Radiative recombination mechanism in GaNxP1- alloys. *Applied Physics Letters*, **2002**, 80, 1740-1742	3.4	59
183	On the Origin of Light Emission in GaNxP1-x. *Materials Research Society Symposia Proceedings*, **2002**, 722, 421		
182	Strain relaxation in GaNxP1- alloy: effect on optical properties. *Physica B: Condensed Matter*, **2001**, 308-310, 106-109	2.8	3
181	Optical properties of GaNAs/GaAs structures. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 143-147	3.1	14
180	Properties of GaAsN/GaAs quantum wells studied by optical detection of cyclotron resonance. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 218-220	3.1	3
179	Magneto-photoluminescence studies of Cd(Mn)Se/Zn(Mn)Se diluted magnetic nanostructures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2001**, 10, 362-367	3	2
178	The 3.466 eV Bound Exciton in GaN. *Physica Status Solidi (B): Basic Research*, **2001**, 228, 489-492	1.3	5
177	Electronic Properties of Ga(In)NAs Alloys. *MRS Internet Journal of Nitride Semiconductor Research*, **2001**, 6, 1		157
176	Structural properties of a GaNxP1- alloy: Raman studies. *Applied Physics Letters*, **2001**, 78, 3959-3961	3.4	23
175	Signature of an intrinsic point defect in GaNxAs1-. *Physical Review B*, **2001**, 63,	3.3	50
174	Formation of nonradiative defects in molecular beam epitaxial GaNxAs1- studied by optically detected magnetic resonance. *Applied Physics Letters*, **2001**, 79, 3089-3091	3.4	59
173	Spin Polarization and Injection in ZnMnSe/ZnCdSe Heterostructures. *Materials Research Society Symposia Proceedings*, **2001**, 690, F1.7.1		
172	Nature and Formation of Non-Radiative Defects in GaNAs And InGaAsN. *Materials Research Society Symposia Proceedings*, **2001**, 692, 1		7
171	Raman Studies of GaNP Alloy. *Materials Research Society Symposia Proceedings*, **2001**, 693, 567		1
170	Disorder-Activated Resonant Raman Scattering in GaNAs/GaAs Structures. *Springer Proceedings in Physics*, **2001**, 73-74	0.2	
169	Recombination Processes of GaNAs/GaAs structures: Effect of Rapid Thermal Annealing. *Springer Proceedings in Physics*, **2001**, 559-560	0.2	
168	The 3.466 eV Bound Exciton in GaN **2001**, 228, 489		1
167	Optically detected magnetic resonance of semiconductor thin films and layered structures **2000**, 4086, 44		

166	Applications of optically detected magnetic resonance in semiconductor layered structures. *Thin Solid Films*, **2000**, 364, 45-52	2.2	51
165	Applications of defect engineering in InP-based structures. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 75, 103-109	3.1	2
164	Photoluminescence characterization of GaNAs/GaAs structures grown by molecular beam epitaxy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 75, 166-169	3.1	11
163	The Carbon Vacancy Pair in 4H and 6H SiC. *Materials Science Forum*, **2000**, 338-342, 821-824	0.4	6
162	Ga-related defect in as-grown Zn-doped GaN: An optically detected magnetic resonance study. *Physical Review B*, **2000**, 62, R10607-R10609	3.3	10
161	Type I band alignment in the GaNxAs1□/GaAs quantum wells. *Physical Review B*, **2000**, 63,	3.3	50
160	Silicon vacancy related defect in 4H and 6H SiC. *Physical Review B*, **2000**, 61, 2613-2620	3.3	202
159	Direct determination of electron effective mass in GaNAs/GaAs quantum wells. *Applied Physics Letters*, **2000**, 77, 1843	3.4	156
158	Magneto-optical studies of the 0.88-eV photoluminescence emission in electron-irradiated GaN. *Physical Review B*, **2000**, 62, 16572-16577	3.3	10
157	Electronic structure of the neutral silicon vacancy in 4H and 6H SiC. *Physical Review B*, **2000**, 62, 16555-16560	3.3	65
156	Optically detected cyclotron resonance investigations on 4H and 6H SiC: Band-structure and transport properties. *Physical Review B*, **2000**, 61, 4844-4849	3.3	21
155	Hole effective masses in 4H SiC. *Physical Review B*, **2000**, 61, R10544-R10546	3.3	36
154	Bandstructure and Transport Properties of 4H- and 6H-SiC: Optically Detected Cyclotron Resonance Investigations. *Materials Science Forum*, **2000**, 338-342, 559-562	0.4	1
153	Hole Effective Masses in 4H SiC Determined by Optically Detected Cyclotron Resonance. *Materials Science Forum*, **2000**, 338-342, 563-566	0.4	
152	Mechanism for rapid thermal annealing improvements in undoped GaNxAs1□/GaAs structures grown by molecular beam epitaxy. *Applied Physics Letters*, **2000**, 77, 2325-2327	3.4	87
151	Effect of zinc substitution on internal friction in YBCO superconductors. *Superconductor Science and Technology*, **1999**, 12, 645-648	3.1	7
150	Thermal stability and doping efficiency of intrinsic modulation doping in InP-based structures. *Applied Physics Letters*, **1999**, 75, 1733-1735	3.4	1
149	Electronic structure of the 0.88-eV luminescence center in electron-irradiated gallium nitride. *Physical Review B*, **1999**, 60, 1746-1751	3.3	2

148	Photoluminescence and Zeeman effect in chromium-doped 4H and 6H SiC. *Journal of Applied Physics*, **1999**, 86, 4348-4353	2.5	31
147	Mechanism of radiative recombination in acceptor-doped bulk GaN crystals. *Physica B: Condensed Matter*, **1999**, 273-274, 39-42	2.8	12
146	Electron-paramagnetic-resonance studies of defects in electron-irradiated p-type 4H and 6H SiC. *Physica B: Condensed Matter*, **1999**, 273-274, 655-658	2.8	8
145	Zeeman spectroscopy of the neutral silicon vacancy in 6H and 4H SiC. *Physica B: Condensed Matter*, **1999**, 273-274, 663-666	2.8	1
144	Carbon-vacancy related defects in 4H- and 6H-SiC. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 61-62, 202-206	3.1	28
143	Intrinsic modulation doping in InP-based structures: properties relevant to device applications. *Journal of Crystal Growth*, **1999**, 201-202, 786-789	1.6	
142	Mechanism for low-temperature photoluminescence in GaNAs/GaAs structures grown by molecular-beam epitaxy. *Applied Physics Letters*, **1999**, 75, 501-503	3.4	227
141	Mechanism for Light Emission in GaNAs/GaAs Structures Grown by Molecular Beam Epitaxy. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 125-129	1.3	8
140	Effect of growth temperature on photoluminescence of GaNAs/GaAs quantum well structures. *Applied Physics Letters*, **1999**, 75, 3781-3783	3.4	55
139	Optically detected magnetic resonance studies of intrinsic defects in 6H-SiC. *Semiconductor Science and Technology*, **1999**, 14, 1141-1146	1.8	28
138	A Complex Defect Related to the Carbon Vacancy in 4H and 6H SiC. *Physica Scripta*, **1999**, T79, 46	2.6	9
137	Effect of Electron Irradiation on Optical Properties of Gallium Nitride. *Physica Scripta*, **1999**, T79, 72	2.6	5
136	Role of the Substitutional Oxygen Donor in the Residual N-Type Conductivity in GaN. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 514-519		1
135	Optically Detected Magnetic Resonance Studies of Non-Radiative Recombination Centres in 6H SiC. *Materials Science Forum*, **1998**, 264-268, 599-602	0.4	6
134	The Neutral Silicon Vacancy in 6H and 4H SiC. *Materials Science Forum*, **1998**, 264-268, 473-476	0.4	8
133	On the improvement in thermal quenching of luminescence in SiGe/Si structures grown by molecular beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 1928		
132	Photoluminescence of GaN: Effect of electron irradiation. *Applied Physics Letters*, **1998**, 73, 2968-2970	3.4	55
131	Properties of Er-related emission in in situ doped Si epilayers grown by molecular beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 1732		7

130	Chen et al. Reply:. *Physical Review Letters*, **1998**, 80, 423-423	7.4	5
129	Similarity between the 0.88-eV photoluminescence in GaN and the electron-capture emission of the OP donor in GaP. *Physical Review B*, **1998**, 58, R13351-R13354	3.3	15
128	Chromium in 4H and 6H SiC: Photoluminescence and Zeeman Studies. *Materials Science Forum*, **1998**, 264-268, 603-606	0.4	4
127	Influence of Growth Conditions on the Thermal Quenching of Photoluminescence From Sige/Si Quantum Structures. *Materials Research Society Symposia Proceedings*, **1998**, 533, 295		
126	Role of the Substitutional Oxygen Donor in the Residual N-Type Conductivity in GaN. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		
125	Optical properties of electron-irradiated GaN. *MRS Internet Journal of Nitride Semiconductor Research*, **1998**, 3, 1		6
124	Strong effects of carrier concentration on the Fermi-edge singularity in modulation-doped InP/InxGa1□As heterostructures. *Physical Review B*, **1997**, 55, 7052-7058	3.3	11
123	Er/O and Er/F doping during molecular beam epitaxial growth of Si layers for efficient 1.54 □m light emission. *Applied Physics Letters*, **1997**, 70, 3383-3385	3.4	36
122	Effects of microwave fields on recombination processes in 4H and 6H SiC. *Journal of Applied Physics* , **1997**, 81, 1929-1932	2.5	4
121	The Role of Non-Radiative Defects in Thermal Quenching of Luminescence in SiGe/Si Structures Grown by Molecular Beam Epitaxy. *Materials Science Forum*, **1997**, 258-263, 139-144	0.4	
120	Intrinsic Modulation Doping in InP-Based Heterostructures. *Materials Science Forum*, **1997**, 258-263, 805-812	0.4	1
119	A Deep Photoluminescence Band in 4H SiC Related to the Silicon Vacancy. *Materials Science Forum*, **1997**, 258-263, 685-690	0.4	5
118	Mbe Growth And Characterization Of Er/O And Er/F Doped Si Light Emitting Structures. *Materials Research Society Symposia Proceedings*, **1997**, 486, 133		
117	Postgrowth hydrogen treatments of nonradiative defects in low-temperature molecular beam epitaxial Si. *Applied Physics Letters*, **1997**, 70, 369-371	3.4	7
116	Optically detected magnetic resonance studies of defects in electron-irradiated 3C SiC layers. *Physical Review B*, **1997**, 55, 2863-2866	3.3	33
115	Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers. *Diamond and Related Materials*, **1997**, 6, 1381-1384	3.5	2
114	Deep luminescent centres in electron-irradiated 6H SiC. *Diamond and Related Materials*, **1997**, 6, 1378-1380	3.5	8
113	Mechanism for thermal quenching of luminescence in SiGe/Si structures grown by molecular beam epitaxy: Role of nonradiative defects. *Applied Physics Letters*, **1997**, 71, 3676-3678	3.4	25

112	Effective Masses in SiC Determined by Cyclotron Resonance Experiments. *Physica Status Solidi A*, **1997**, 162, 79-93		20
111	Effective Masses in SiC Determined by Cyclotron Resonance Experiments **1997**, 162, 79		1
110	Determination of the electron effective-mass tensor in 4H SiC. *Physical Review B*, **1996**, 53, 15409-15412	3.3	60
109	Intrinsic N-Type Modulation Doping in InP-Based Heterostructures. *Materials Research Society Symposia Proceedings*, **1996**, 421, 21		
108	Defects in Low Temperature MBE-Grown Si and SiGe/Si Structures. *Materials Research Society Symposia Proceedings*, **1996**, 442, 355		1
107	Optical properties of boron modulation-doped SiGe quantum wells and Si thin films. *Solid-State Electronics*, **1996**, 40, 53-57	1.7	
106	Important defect aspects in optoelectronic applications of Si- and SiGe/Si-heterostructures. *Applied Surface Science*, **1996**, 102, 279-282	6.7	
105	Influence of growth conditions on the formation of deep photoluminescence bands in MBE-grown Si layers and SiGe/Si quantum structures. *Applied Surface Science*, **1996**, 102, 293-297	6.7	4
104	Intense photoluminescence observed in modulation doped Si/SiGe quantum well structures. *Applied Surface Science*, **1996**, 102, 298-302	6.7	1
103	Fermi-edge singularity in p-type modulation-doped SiGe quantum wells. *Physical Review B*, **1996**, 53, R1701-R1704	3.3	4
102	Nonradiative defects in Si and SiGe/Si heterostructures grown by molecular beam epitaxy. *Applied Physics Letters*, **1996**, 68, 1256-1258	3.4	8
101	Intrinsic Doping: A New Approach for n-Type Modulation Doping in InP-Based Heterostructures. *Physical Review Letters*, **1996**, 77, 2734-2737	7.4	18
100	Photoluminescence of the two-dimensional hole gas in p-type delta -doped Si layers. *Physical Review B*, **1996**, 53, 9587-9590	3.3	17
99	The ordered□disordered transition in Si delta-doped GaAs. *Applied Physics Letters*, **1996**, 68, 3464-3466	3.4	5
98	Identification of Grown-In Efficient Nonradiative Recombination Centers in Molecular Beam Epitaxial Silicon. *Physical Review Letters*, **1996**, 77, 4214-4217	7.4	14
97	Dominant recombination center in electron-irradiated 3C SiC. *Journal of Applied Physics*, **1996**, 79, 3784-3786	2.5	28
96	Optical detection of quantum oscillations in InP/InGaAs quantum structures. *Applied Physics Letters*, **1996**, 69, 809-811	3.4	9
95	Influence of ion bombardment on Si and SiGe films during molecular beam epitaxy growth. *Applied Physics Letters*, **1996**, 68, 238-240	3.4	14

94	Radiative recombination processes in p-type modulation-doped SiGe quantum wells and Si epilayers. *Journal of Crystal Growth*, **1995**, 157, 362-366	1.6	
93	Some critical issues on growth of high quality Si and SiGe films using a solid-source molecular beam epitaxy system. *Journal of Crystal Growth*, **1995**, 157, 242-247	1.6	8
92	Shallow excited states of deep luminescent centers in silicon. *Solid State Communications*, **1995**, 93, 415-418	1.6	6
91	Optically detected cyclotron-resonance studies of radiative processes in AlxGa1-xAs/GaAs high-electron-mobility structures. *Physical Review B*, **1995**, 52, 14688-14692	3.3	5
90	Chen et al. reply. *Physical Review Letters*, **1995**, 75, 3963	7.4	1
89	Effect of ion bombardment on deep photoluminescence bands in p-type boron-modulation-doped Si layers grown by molecular-beam epitaxy. *Physical Review B*, **1995**, 52, 12006-12012	3.3	8
88	Efficient excitation transfer in silicon studied by Fourier transform photoluminescence excitation spectroscopy. *Applied Physics Letters*, **1995**, 66, 1498-1500	3.4	1
87	High quality 4H-SiC epitaxial layers grown by chemical vapor deposition. *Applied Physics Letters*, **1995**, 66, 1373-1375	3.4	45
86	Transfer mechanism between pseudodonor excited singlet and triplet states of the S-Cu complex defect in silicon. *Physical Review B*, **1995**, 52, 8848-8853	3.3	7
85	Optically detected magnetic-resonance study of a metastable selenium-related center in silicon. *Physical Review B*, **1995**, 51, 2132-2136	3.3	12
84	Important Nonradiative Grown-In Defects in MBE-Grown Si and SiGe/Si Heterostructures. *Materials Science Forum*, **1995**, 196-201, 473-478	0.4	2
83	Defect Formation and Recombination Processes in p-Type Modulation-Doped Si Epilayers. *Materials Science Forum*, **1995**, 196-201, 479-484	0.4	
82	Properties of deep photoluminescence bands in SiGe/Si quantum structures grown by molecular beam epitaxy. *Applied Physics Letters*, **1995**, 67, 1642-1644	3.4	8
81	Electron effective masses in 4H SiC. *Applied Physics Letters*, **1995**, 66, 1074-1076	3.4	89
80	Efficient Nonradiative Recombination Centers in MBE-Grown Si and SiGe/Si Heterostructures. *Materials Research Society Symposia Proceedings*, **1995**, 378, 135		1
79	Radiative Recombination Processes in Boron Modulation-Doped SiGe Quantum Wells. *Materials Research Society Symposia Proceedings*, **1995**, 378, 881		1
78	Deep Photoluminescence Bands in MBE Grown Si and SiGe. *Materials Research Society Symposia Proceedings*, **1995**, 379, 405		1
77	Response to "Comment on 'Mechanism responsible for the semi-insulating properties of low-temperature-grown GaAs'" [Appl. Phys. Lett. 67, 1331 (1995)]. *Applied Physics Letters*, **1995**, 67, 1333-1334	3.4	6

76	Possible lifetime-limiting defect in 6H SiC. *Applied Physics Letters*, **1994**, 65, 2687-2689	3.4	25
75	Direct determination of the electron-electron-hole Auger threshold energy in silicon. *Physical Review Letters*, **1994**, 73, 3258-3261	7.4	4
74	Metastable chalcogen-related luminescent centers in silicon. *Physical Review B*, **1994**, 49, 1662-1667	3.3	6
73	S-Cu-related metastable complex defect in Si by optical detection of magnetic resonance. *Physical Review B*, **1994**, 50, 7365-7370	3.3	6
72	Observation of rapid direct charge transfer between deep defects in silicon. *Physical Review Letters* , **1994**, 72, 2939-2942	7.4	37
71	Application of the ODCR experiment to the identification of radiative recombination processes. *Journal of Luminescence*, **1994**, 60-61, 52-55	3.8	2
70	Mechanism responsible for the semi-insulating properties of low-temperature-grown GaAs. *Applied Physics Letters*, **1994**, 65, 3002-3004	3.4	116
69	Optical detection of cyclotron resonance for characterization of recombination processes in semiconductors. *Critical Reviews in Solid State and Materials Sciences*, **1994**, 19, 241-301	10.1	47
68	Electron effective masses and mobilities in high-purity 6HSiC chemical vapor deposition layers. *Applied Physics Letters*, **1994**, 65, 3209-3211	3.4	65
67	Origin of n-type conductivity of low-temperature grown InP. *Journal of Applied Physics*, **1994**, 76, 600-602	2.5	27
66	SiC a semiconductor for high-power, high-temperature and high-frequency devices. *Physica Scripta*, **1994**, T54, 283-290	2.6	24
65	Mechanism of the configurational change of metastable defects in silicon. *Physical Review Letters*, **1993**, 71, 416-419	7.4	12
64	Phosphorus antisite defects in low-temperature InP. *Physical Review B*, **1993**, 47, 4111-4114	3.3	57
63	Magnetic Resonance Techniques for Excited State Spectroscopy of Defects in Silicon. *Materials Science Forum*, **1993**, 143-147, 1345-1352	0.4	1
62	Electronic Structure of PIn Antisite in InP. *Materials Science Forum*, **1993**, 143-147, 211-216	0.4	2
61	Observation of Rapid Direct Charge Transfer between Deep Defects in Silicon. *Materials Science Forum*, **1993**, 143-147, 1371-1374	0.4	1
60	The Configurational Change of a Metastable S-Cu Defect in Silicon. *Materials Science Forum*, **1993**, 143-147, 1179-1184	0.4	3
59	Optically Detected Cyclotron Resonance for Defect Characterization. *Materials Science Forum*, **1993** , 143-147, 1353-1358	0.4	1

58	Properties of Resonant Localized Donor Level in Low-Temperature-Grown InP. *Materials Science Forum*, **1993**, 143-147, 1081-1086	0.4	0
57	A Metastable Selenium-Related Center in Silicon. *Materials Science Forum*, **1993**, 143-147, 159-164	0.4	2
56	Electronic properties of low-temperature InP. *Journal of Electronic Materials*, **1993**, 22, 1487-1490	1.9	15
55	Optically detected magnetic resonance studies of low-temperature InP. *Journal of Electronic Materials*, **1993**, 22, 1491-1494	1.9	15
54	Effects of a hot two-dimensional electron gas on optical properties of modulation-doped GaAs/AlGaAs heterostructures. *Semiconductor Science and Technology*, **1992**, 7, B253-B255	1.8	7
53	Optical detection of chaotic oscillations owing to impact ionization of donors by hot carriers in GaInAs. *Semiconductor Science and Technology*, **1992**, 7, B483-B485	1.8	1
52	ODMR and Electron Spin Echo Studies on the Non-Radiative Triplet State of the (V-O)⁻ Defect in Silicon. *Materials Science Forum*, **1992**, 83-87, 357-362	0.4	3
51	Magnetic Resonance from a Metastable Sulfur-Pair-Related Complex Defect in Silicon. *Materials Science Forum*, **1992**, 83-87, 251-256	0.4	8
50	A New Defect Observed in Annealed Phosphorus-Doped Electron-Irradiated Silicon. *Materials Science Forum*, **1992**, 83-87, 333-338	0.4	2
49	Optical investigation of Fermi-edge singularities in Al0.35Ga0.65As/GaAs heterostructures. *Physical Review B*, **1992**, 46, 4352-4355	3.3	16
48	Zero-field optical detection of magnetic resonance on a metastable sulfur-pair-related defect in silicon: Evidence for a Cu constituent. *Physical Review B*, **1992**, 46, 12316-12322	3.3	22
47	AlGaAs to GaAs Energy Transfer Mechanisms in AlGaAs/GaAs Structures. *Acta Physica Polonica A*, **1992**, 82, 713-716	0.6	
46	Role of free carriers in the application of optically detected magnetic resonance for studies of defects in silicon. *Applied Physics A: Solids and Surfaces*, **1991**, 53, 130-135		25
45	Optically Detected Magnetic Resonance Studies of Bound Exciton Triplets for Complex Defects in GaP. *Materials Science Forum*, **1991**, 38-41, 769-774	0.4	2
44	Optically detected impact-ionization-related chaotic oscillations in Ga0.47In0.53As. *Physical Review B*, **1991**, 44, 8357-8360	3.3	8
43	Direct observation of intercenter charge transfer in dominant nonradiative recombination channels in silicon. *Physical Review Letters*, **1991**, 67, 1914-1917	7.4	39
42	Impact Ionization Driven Chaotic Photoluminescence Oscillations in Ga0.47In0.53As. *Acta Physica Polonica A*, **1991**, 80, 271-274	0.6	
41	Optically Detected Magnetic Resonance Studies of Te-Related Shallow Donors in AlxGa1-xAs. *Acta Physica Polonica A*, **1991**, 80, 341-344	0.6	

40	Time-resolved zero-field optically detected magnetic-resonance study of the (Cu-Li)V neutral defect complex in GaP. *Physical Review B*, **1990**, 42, 1684-1689	3.3	4
39	Defect annealing in electron-irradiated boron-doped silicon. *Physical Review B*, **1990**, 41, 1019-1027	3.3	3
38	Microscopic identification and electronic structure of a di-hydrogen-vacancy complex in silicon by optical detection of magnetic resonance. *Physical Review Letters*, **1990**, 64, 3042-3045	7.4	32
37	Steady-state level-anticrossing spectra for bound-exciton triplets associated with complex defects in semiconductors. *Physical Review B*, **1990**, 41, 5746-5755	3.3	17
36	Intensity of exciton luminescence in silicon in a weak magnetic field. *Physical Review B*, **1990**, 42, 5120-5125	3.3	5
35	Delayed optical detection of magnetic resonance for defects in Si and GaAs. *Journal of Applied Physics*, **1990**, 68, 2506-2509	2.5	9
34	Characterization of GaAs/AlGaAs heterojunctions by optical detection of cyclotron resonance. *Surface Science*, **1990**, 229, 484-487	1.8	7
33	Optical characterization of a deep (Cu-C)-related complex defect in GaP. *Physical Review B*, **1989**, 39, 3153-3158	3.3	3
32	Gai self-interstitial-related defect in GaP studied by optically detected magnetic resonance. *Physical Review B*, **1989**, 40, 1365-1368	3.3	12
31	Optically detected magnetic resonance of a thermally induced deep center in electron-irradiated silicon. *Physical Review B*, **1989**, 40, 10013-10016	3.3	3
30	Hot-Carrier Effects on Optical Properties of GaAs/AlxGai1-xAs Quantum Wells. *Materials Research Society Symposia Proceedings*, **1989**, 160, 707		3
29	Optically Detected Magnetic Resonance of a Hydrogen-Related Complex Defect in Silicon. *Materials Research Society Symposia Proceedings*, **1989**, 163, 377		
28	Electronic structure of complex defects in semiconductors from luminescence perturbation spectroscopy. *Journal of Luminescence*, **1988**, 40-41, 59-63	3.8	2
27	Complex defects in gap studied by optically detected magnetic resonance (ODMR). *Journal of Luminescence*, **1988**, 40-41, 337-338	3.8	
26	Optically detected magnetic resonance studies of the 1.911-eV Cu-related complex in GaP. *Physical Review B*, **1988**, 37, 2558-2563	3.3	12
25	Two deep (PGa-Cu)-related neutral complex defects in GaP studied with optically detected magnetic resonance. *Physical Review B*, **1988**, 37, 2564-2569	3.3	12
24	Effects of interlevel coupling on optically detected magnetic resonance spectra for complex defects in semiconductors. *Physical Review B*, **1988**, 38, 12660-12663	3.3	5
23	Spin-forbidden Delta ms=2 transitions in the optically detected magnetic-resonance spectra of excitons bound at complex neutral defects in GaP. *Physical Review B*, **1988**, 37, 8795-8804	3.3	2

22	Transfer processes for excitons bound to complex defects in GaP studied by optical detection of magnetic resonance. *Physical Review B*, **1988**, 37, 2570-2577	3.3	26
21	Investigation of the (Cu-Li)-related 2.172-eV bound exciton in GaP with optically detected magnetic resonance. *Physical Review B*, **1988**, 38, 1191-1196	3.3	5
20	"Forbidden" electronic- and nuclear-spin transitions in optically detected magnetic resonance spectra of deep complex defects in GaP. *Physical Review B*, **1988**, 37, 6555-6558	3.3	1
19	ELECTRONIC STRUCTURE OF BOUND EXCITONS IN SEMICONDUCTORS **1987**, 256-285		1
18	Electronic properties of a (Cu-Li)-related neutral complex defect with a bound exciton at 2.25 eV in GaP. *Physical Review B*, **1987**, 36, 7948-7954	3.3	9
17	Electronic structure of a hole-attractive neutral Cu-related complex-defect bound exciton at 2.345 eV in ZnTe. *Physical Review B*, **1987**, 35, 5722-5728	3.3	13
16	Electronic properties of a complex Cu-related acceptor with a bound exciton at 2.3423 eV in ZnTe. *Physical Review B*, **1987**, 35, 5714-5721	3.3	7
15	PGa-antisite-related neutral complex defect in GaP studied with optically detected magnetic resonance. *Physical Review B*, **1987**, 36, 5058-5061	3.3	18
14	Direct evidence for efficient energy transfer from N-related defects to PGa antisite complexes in GaP from optically detected magnetic resonance. *Physical Review B*, **1987**, 36, 7755-7757	3.3	5
13	Spectroscopy of Impurities and Complex Defects in Silicon in Electric and Microwave Fields. *Materials Research Society Symposia Proceedings*, **1987**, 104, 117		6
12	Optical Detection of Magnetic Resonance (ODMR) Studies of the Electronic Structure of Complex Defects in GaP. *Materials Research Society Symposia Proceedings*, **1987**, 104, 443		
11	Optically Detected Magnetic Resonance Studies of Complex Antisite-Related Defects in Bulk LEC GaP. *Materials Research Society Symposia Proceedings*, **1987**, 104, 467		1
10	Electronic structure of the 2.3149-eV complex defect in Ag-doped ZnTe. *Physical Review B*, **1987**, 36, 4831-4835	3.3	10
9	Electronic structure of bound excitons in semiconductors. *Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics*, **1987**, 146, 256-285		29
8	Properties of shallow Li-related donors in GaP from optically detected magnetic resonance. *Physical Review B*, **1986**, 33, 8246-8253	3.3	14
7	Optical properties and excitation-induced distortions of a trigonal Cu-related neutral complex with a bound exciton at 2.26 eV in ZnTe. *Physical Review B*, **1986**, 34, 8656-8666	3.3	16
6	Electronic Structure of Neutral Complex Defects in Silicon. *Materials Science Forum*, **1986**, 10-12, 97-102	0.4	1
5	Electronic properties of an electron-attractive complex neutral defect in GaAs. *Physical Review B*, **1986**, 33, 4424-4427	3.3	14

4	Optically detected magnetic resonance investigation of a deep Li-related complex in GaP. *Physical Review B*, **1985**, 32, 6650-6654	3.3	16
3	Electromagnetic instability in interpenetrating electron-ion plasmas. *Physics of Fluids*, **1973**, 16, 277		1
2	On the Origin of Seebeck Coefficient Inversion in Highly Doped Conducting Polymers. *Advanced Functional Materials*,2112276	15.6	2
1	Room-temperature electron spin polarization exceeding 90% in an opto-spintronic semiconductor nanostructure via remote spin filtering. *Nature Photonics*,	33.9	7